

# 650V SiC Schottky Diode

### **FEATURES**

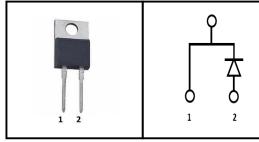
- Low Conduction and Swiitch Loss
- Positive Temperature Coefficient on VF
- Temperature Independent Switching Behavior
- Fast Reverse Recovery
- High Surge Current Capability
- Pb-free lead plating

### **BENEFITS**

- Higher System Efficiency
- Parallel Device Convenience
- High Temperature Application
- High Frequency Operation
- Hard Switching & High Reliability
- Environmental Protection

### **APPLICATIONS**

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- Solar/ Wind Renewable Energy
- Power Inverters
- Motor Drives





| Device Marking and Package Information |           |             |  |  |
|--|-----------|-------------|--|--|
| Device                                 | Package   | Marking     |  |  |
| C2S065H010B                            | TO-220-2L | C2S065H010B |  |  |

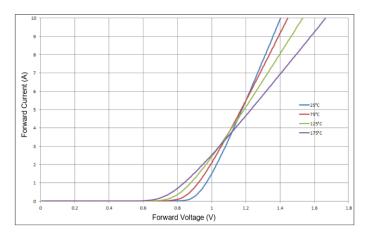
| Absolute Maximum Ratings T <sub>C</sub> = 25°C, unless otherwise noted |                                   |   |         |      |  |
|--|-----------------------------------|---|---------|------|--|
| Parameter  | Symbol                            | Test Conditions                                     | Value   | Unit |  |
| Peak Repetitive Reverse Voltage  | $V_{RRM}$                         | T <sub>J</sub> = 25°C                               | 650     | V    |  |
| Peak Reverse Surge Voltage   | V <sub>RSM</sub>                  | T <sub>J</sub> = 25°C                               | 650     | V    |  |
| DC Blocking Voltage  | $V_R$                             | T <sub>J</sub> = 25°C                               | 650     | V    |  |
| Continuous Forward Current   | I <sub>F</sub>                    | T <sub>J</sub> ≤ 135°C                              | 10      | Α    |  |
| Repetitive Peak Forward Surge Current                                  | I <sub>FRM</sub>                  | $T_C = 25^{\circ}C$ , $T_P = 8.3$ ms Half Sine Wave | 85      | А    |  |
| Maximum Case Temperature   | T <sub>C</sub>                    |   | 135     | °C   |  |
| Operating Junction and Storage<br>Temperature                          | T <sub>J</sub> , T <sub>stg</sub> |   | -55~175 | °C   |  |

| Thermal Resistance                   |                   |       |      |  |  |
|--------------------------------------|-------------------|-------|------|--|--|
| Parameter                            | Symbol            | Value | Unit |  |  |
| Thermal Resistance, Junction-to-Case | R <sub>thJC</sub> | 1.1   | °C/W |  |  |



| Specifications T <sub>J</sub> = 25°C, unless otherwise noted |                |   |       |      |      |  |  |
|--|----------------|---|-------|------|------|--|--|
| B  | Symbol         | Tool Conditions   | Value |      | 1114 |  |  |
| Parameter  |                | Test Conditions   | Тур.  | Max. | Unit |  |  |
| Famurand Voltage   | V <sub>F</sub> | I <sub>F</sub> = 10A, T <sub>J</sub> = 25°C                         | 1.4   | 1.65 | V    |  |  |
| Forward Voltage  |                | I <sub>F</sub> = 10A, T <sub>J</sub> = 175°C                        | 1.75  | 2.3  | V    |  |  |
| Reverse Current  | I <sub>R</sub> | V <sub>R</sub> =650V, T <sub>J</sub> = 25°C                         | 1     | 20   | μΑ   |  |  |
|  |                | V <sub>R</sub> =650V, T <sub>J</sub> = 175°C                        | 5     | 100  | μΑ   |  |  |
| Total Capacitive Charge                                      | Q <sub>C</sub> | $I_F = 10A$ , di/dt =200A / $\mu$ s<br>$V_R = 650V$ , $T_J = 25$ °C | 25    |      | nC   |  |  |
| Total Capacitance  | С              | $V_R = 0V, T_J = 25^{\circ}C, f = 1 MHz$                            | 440   | 10   |      |  |  |
|  |                | V <sub>R</sub> =200V, T <sub>J</sub> = 25°C, , f =1 MHz             | 57    |      | pF   |  |  |
|  |                | V <sub>R</sub> =400V, T <sub>J</sub> = 25°C, , f =1 MHz             | 46    |      |      |  |  |





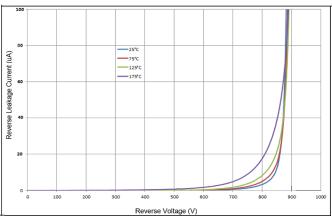
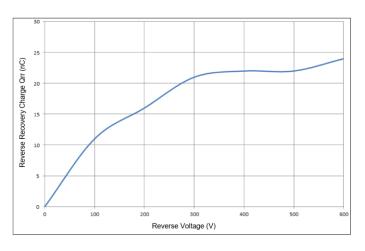


Fig. 1 Forward Characteristics

Fig. 2 Reverse Characteristics



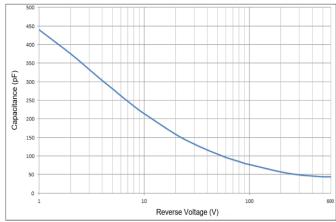


Fig. 3 Total Capacitance Charge vs. Reverse Voltage

Fig. 4 Total Capacitance vs. Reverse Voltage

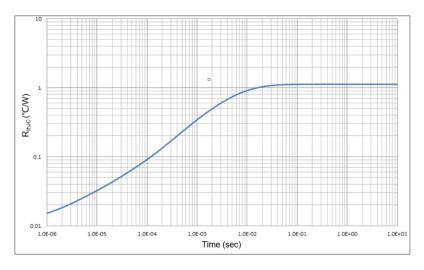
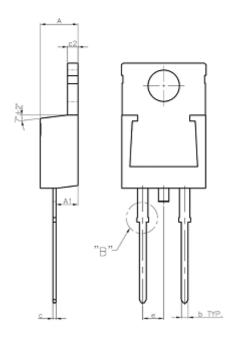


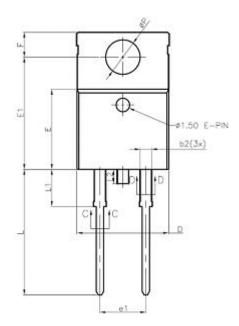
Fig. 5 Transient Thermal Impedance

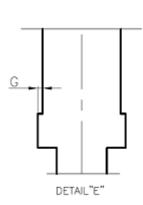


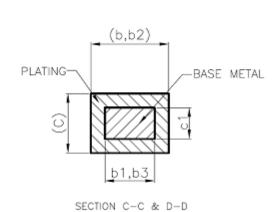
# TO-220-2L



| SYMBOLS | DIMENSIONS IN MILLIMETERS |          |        | DIMENSIONS IN INCHES |           |       |
|---------|---------------------------|----------|--------|----------------------|-----------|-------|
| STMBULS | MIN                       | NOM      | MAX    | MIN                  | NOM       | MAX   |
| A       | 4.470                     |          | 4.670  | 0.176                |           | 0.184 |
| A1      | 2.520                     |          | 2.820  | 0.099                |           | 0.111 |
| b       | 0.710                     | 0.813    | 0.910  | 0.028                | 0.032     | 0.036 |
| b1      | 0.710                     |          | 0.910  | 0.028                |           | 0.036 |
| ь2      | 1.170                     | 1.270    | 1.370  | 0.046                | 0.050     | 0.054 |
| b3      | 1.170                     |          | 1.370  | 0.046                |           | 0.054 |
| С       | 0.279                     |          | 0.483  | 0.011                |           | 0.019 |
| c1      | 0.279                     |          | 0.432  | 0.011                |           | 0.017 |
| c2      | 1.170                     |          | 1.370  | 0.046                |           | 0.054 |
| D       | 10.010                    |          | 10.310 | 0.394                |           | 0.406 |
| E       | 8.763                     | 8.890    | 9.017  | 0.345                | 0.350     | 0.355 |
| E1      | 12.294                    | 12.446   | 12.548 | 0.484                | 0.490     | 0.494 |
| е       |                           | 2.54 BSC |        |                      | 0.100 BSC |       |
| e1      | 4.980                     |          | 5.180  | 0.196                |           | 0.204 |
| F       | 2.642                     | 2.743    | 2.946  | 0.104                | 0.108     | 0.116 |
| G       | 0.000                     |          | 0.127  | 0.000                |           | 0.005 |
| L       | 13.700                    |          | 14.10  | 0.539                |           | 0.555 |
| L1      | 4.04                      | 4.11     | 4.19   | 0.159                | 0.162     | 0.165 |
| L2      |                           |          | 1.60   |                      |           | 0.063 |
| øP      | 3.790                     |          | 3.890  | 0.149                |           | 0.153 |







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